Renesas Electronics America Inc - R5F21207KFP#U1 Datasheet

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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Obsolete
Core Processor	R8C
Core Size	16-Bit
Speed	16MHz
Connectivity	I²C, LINbus, SIO, SSU, UART/USART
Peripherals	POR, Voltage Detect, WDT
Number of I/O	41
Program Memory Size	48KB (48K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	2.5K x 8
Voltage - Supply (Vcc/Vdd)	2.7V ~ 5.5V
Data Converters	A/D 12x10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 125°C (TA)
Mounting Type	Surface Mount
Package / Case	48-LQFP
Supplier Device Package	48-LQFP (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f21207kfp-u1

1.2 Performance Overview

Table 1.1 outlines the Functions and Specifications for R8C/20 Group and Table 1.2 outlines the Functions and Specifications for R8C/21 Group.

Table 1.1 Functions and Specifications for R8C/20 Group

Item		Specification
CPU	Number of fundamental instructions	89 instructions
	Minimum instruction execution time	50 ns (f(XIN) = 20 MHz, VCC = 3.0 to 5.5 V) 100 ns (f(XIN) = 10 MHz, VCC = 2.7 to 5.5 V)
	Operating mode	Single-chip
	Address space	1 Mbyte
	Memory capacity	Refer to **Table 1.3 Product Information for R8C/20 Group**
Peripheral Function	Ports	I/O ports: 41 pins, Input port: 3 pins
	Timers	Timer RA: 8 bits x 1 channel, Timer RB: 8 bits x 1 channel (Each timer equipped with 8-bit prescaler) Timer RD: 16 bits x 2 channel (Circuits of input capture and output compare) Timer RE: With compare match function
	Serial interface	1 channel (UART0) Clock synchronous I/O, UART 1 channel (UART1) UART
	Clock synchronous serial interface	1 channel I2C bus interface(2), Clock synchronous serial I/O with chip select
	LIN module	Hardware LIN: 1 channel (timer RA, UART0)
	A/D converter	10-bit A/D converter: 1 circuit, 12 channels
	Watchdog timer	15 bits x 1 channel (with prescaler) Reset start selectable
	Interrupt	Internal: 11 sources, External: 5 sources, Software: 4 sources, Priority level: 7 levels
	Clock generation circuits	2 circuits XIN clock generation circuit (with on-chip feedback resistor) On-chip oscillator (high speed, low speed) High-speed on-chip oscillator has frequency adjustment function.
	Oscillation stop detection function	Stop detection of XIN clock oscillation
	Voltage detection circuit	On-chip
	Power-on reset circuit include	On-chip
Electric Characteristics	Supply voltage	VCC = 3.0 to 5.5 V (f(XIN) = 20 MHz)(J version) VCC = 3.0 to 5.5 V (f(XIN) = 16 MHz)(K version) VCC = 2.7 to 5.5 V (f(XIN) = 10 MHz)
	Current consumption	Typ. 11.0 mA (VCC = 5 V, f(XIN) = 20 MHz, High-speed on-chip oscillator stopping) Typ. 5.3 mA (VCC = 5 V, f(XIN) = 10 MHz, High-speed on-chip oscillator stopping)
Flash Memory	Programming and erasure voltage	VCC = 2.7 to 5.5 V
	Programming and erasure endurance	100 times
Operating Ambient Temperature		-40 to 85°C
		-40 to 125°C (option(1))
Package		48-pin mold-plastic LQFP

NOTES:
1. When using options, be sure to inquire about the specification.
2. I2C bus is a registered trademark of Koninklijke Philips Electronics N.V.

1.4 Product Information

Table 1.3 lists Product Information for R8C/20 Group and Table 1.4 lists Product Information for R8C/21 Group.

Table 1.3 Product Information for R8C/20 Group **Current of Aug. 2008**

Type No.	ROM Capacity	RAM Capacity	Package Type	Remarks	
R5F21206JFP	32 Kbytes	2 Kbytes	PLQP0048KB-A	J version	Flash memory version
R5F21207JFP	48 Kbytes	2.5 Kbytes	PLQP0048KB-A		
R5F21208JFP	64 Kbytes	3 Kbytes	PLQP0048KB-A		
R5F2120AJFP	96 Kbytes	5 Kbytes	PLQP0048KB-A		
R5F2120CJFP	128 Kbytes(1)	6 Kbytes	PLQP0048KB-A		
R5F21206KFP	32 Kbytes	2 Kbytes	PLQP0048KB-A	K version	
R5F21207KFP	48 Kbytes	2.5 Kbytes	PLQP0048KB-A		
R5F21208KFP	64 Kbytes	3 Kbytes	PLQP0048KB-A		
R5F2120AKFP	96 Kbytes	5 Kbytes	PLQP0048KB-A		
R5F2120CKFP	128 Kbytes(1)	6 Kbytes	PLQP0048KB-A		

NOTE:
1. Do not use addresses 20000h to 23FFFh because these areas are used for the emulator debugger. Refer to **23. Notes on Emulator Debugger** of Hardware Manual.

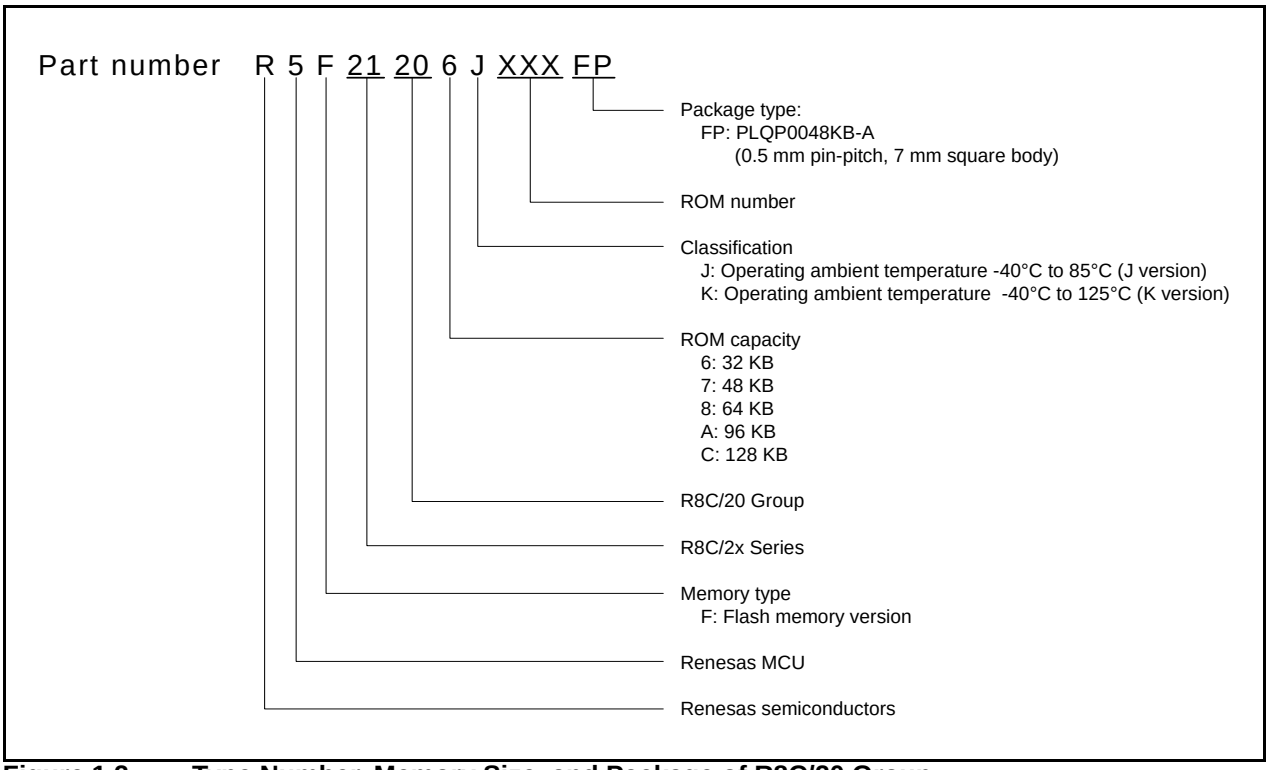


Figure 1.2 Type Number, Memory Size, and Package of R8C/20 Group

Table 1.4 Product Information for R8C/21 Group Current of Aug. 2008

Type No.	ROM Capacity		RAM Capacity	Package Type	Remarks	
	Program ROM	Data Flash				
R5F21216JFP	32 Kbytes	1 Kbyte X 2	2 Kbytes	PLQP0048KB-A	J version	Flash memory version
R5F21217JFP	48 Kbytes	1 Kbyte X 2	2.5 Kbytes	PLQP0048KB-A		
R5F21218JFP	64 Kbytes	1 Kbyte X 2	3 Kbytes	PLQP0048KB-A		
R5F2121AJFP	96 Kbytes	1 Kbyte X 2	5 Kbytes	PLQP0048KB-A		
R5F2121CJFP	128 Kbytes(1)	1 Kbyte X 2	6 Kbytes	PLQP0048KB-A		
R5F21216KFP	32 Kbytes	1 Kbyte X 2	2 Kbytes	PLQP0048KB-A	K version	
R5F21217KFP	48 Kbytes	1 Kbyte X 2	2.5 Kbytes	PLQP0048KB-A		
R5F21218KFP	64 Kbytes	1 Kbyte X 2	3 Kbytes	PLQP0048KB-A		
R5F2121AKFP	96 Kbytes	1 Kbyte X 2	5 Kbytes	PLQP0048KB-A		
R5F2121CKFP	128 Kbytes(1)	1 Kbyte X 2	6 Kbytes	PLQP0048KB-A		

NOTE:
1. Do not use addresses 20000h to 23FFFh because these areas are used for the emulator debugger. Refer to **23. Notes on Emulator Debugger** of Hardware Manual.

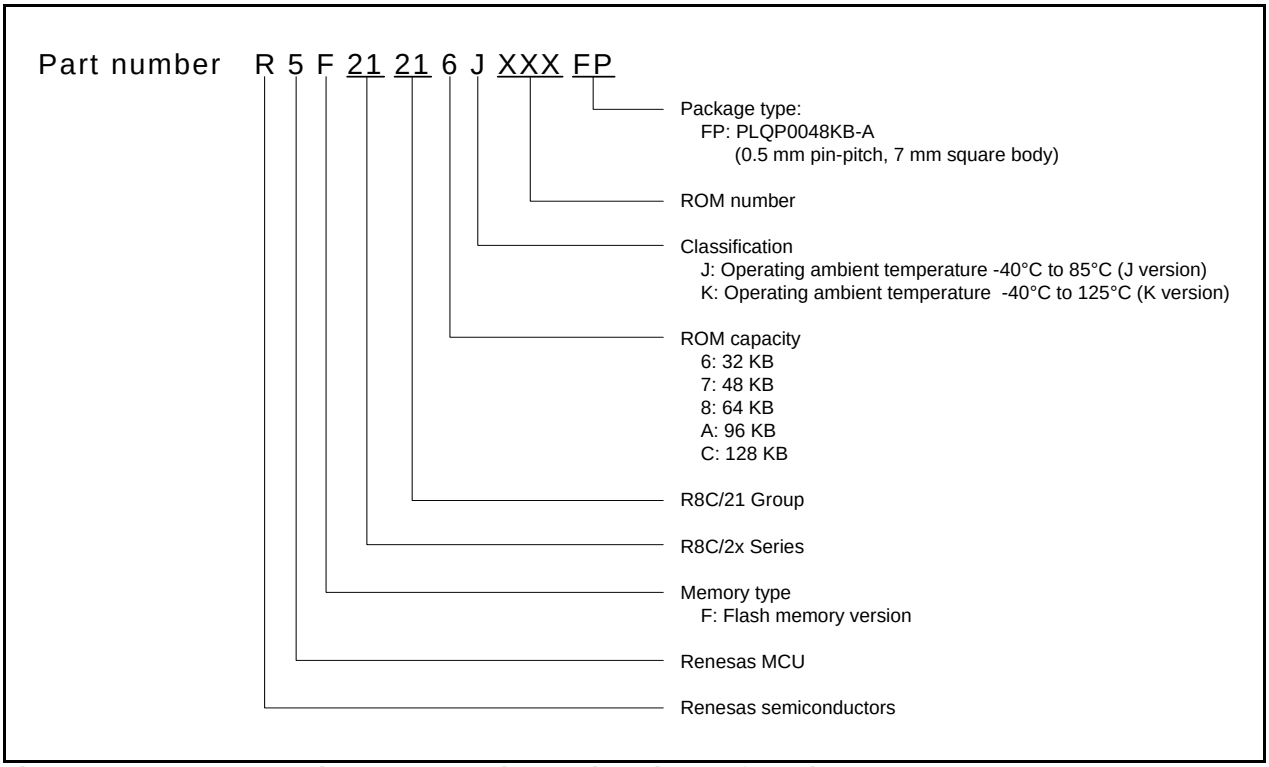


Figure 1.3 Type Number, Memory Size, and Package of R8C/21 Group

1.5 Pin Assignments

Figure 1.4 shows Pin Assignments (Top View).

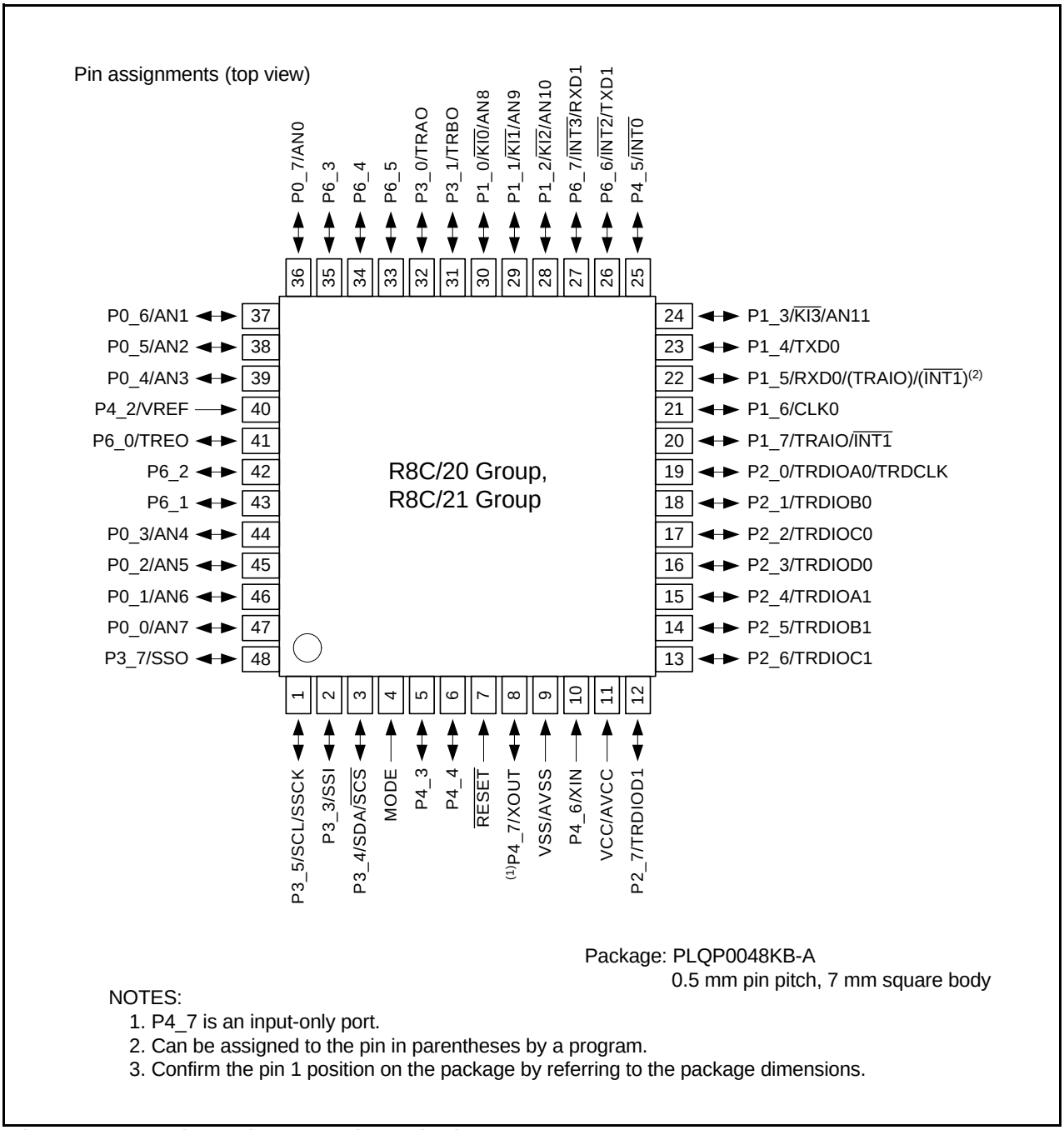


Figure 1.4 Pin Assignments (Top View)

2.8.7 Interrupt Enable Flag (I)

The I flag enables a maskable interrupt.
An interrupt is disabled when the I flag is set to 0, and are enabled when the I flag is set to 1. The I flag is set to 0 when an interrupt request is acknowledged.

2.8.8 Stack Pointer Select Flag (U)

ISP is selected when the U flag is set to 0; USP is selected when the U flag is set to 1.
The U flag is set to 0 when a hardware interrupt request is acknowledged or the INT instruction of software interrupt numbers. 0 to 31 is executed.

2.8.9 Processor Interrupt Priority Level (IPL)

IPL, 3 bits wide, assigns processor interrupt priority levels from level 0 to level 7.
If a requested interrupt has greater priority than IPL, the interrupt is enabled.

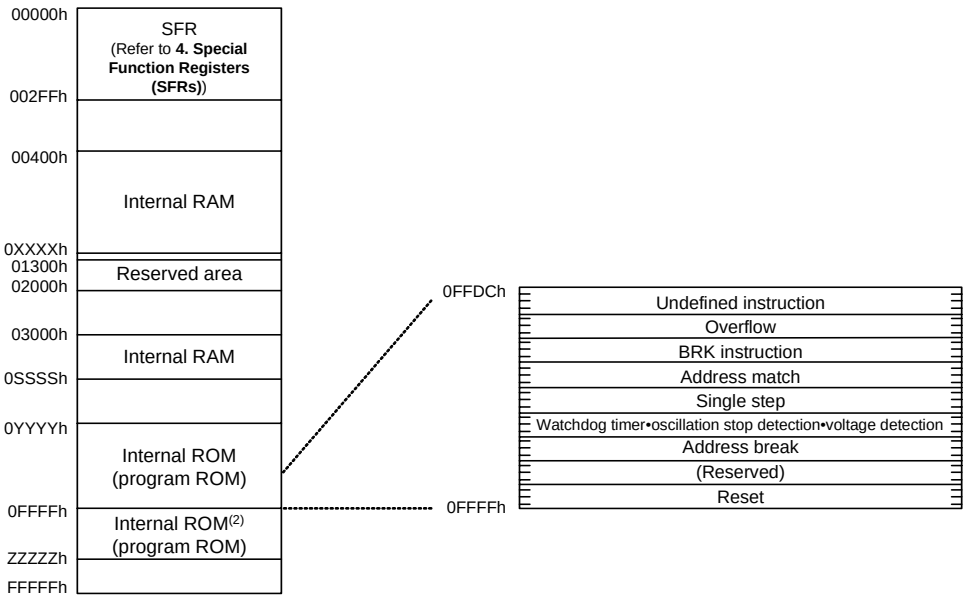
2.8.10 Reserved Bit

If necessary, set to 0. When read, the content is undefined.

3. Memory

3.1 R8C/20 Group

Figure 3.1 shows a Memory Map of R8C/20 Group. The R8C/20 Group has 1 Mbyte of address space from address 00000h to FFFFFh.
The internal ROM is allocated lower addresses, beginning with address 0FFFFh. For example, a 48-Kbyte internal ROM is allocated addresses 04000h to 0FFFFh.
The fixed interrupt vector table is allocated addresses 0FFDCh to 0FFFFh. They store the starting address of each interrupt routine.
The internal RAM is allocated higher addresses, beginning with address 00400h. For example, a 2.5-Kbyte internal RAM is allocated addresses 00400h to 00DFFh. The internal RAM is used not only for storing data but also for calling subroutines and as stacks when interrupt requests are acknowledged.
Special function registers (SFR) are allocated addresses 00000h to 002FFh. The peripheral function control registers are allocated here. All addresses within the SFR, which have nothing allocated are reserved for future user and cannot be accessed by users.



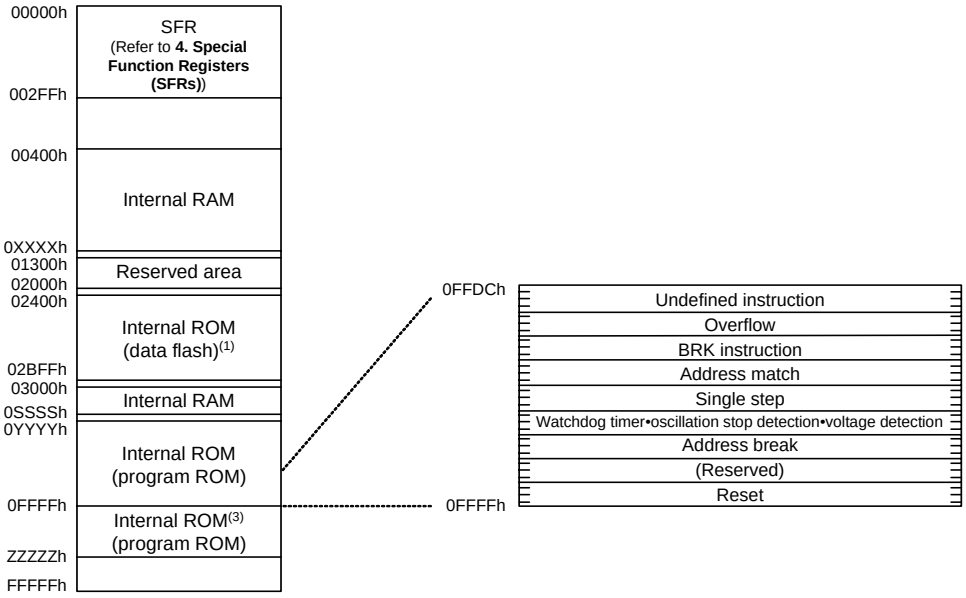
NOTES:
1. The blank regions are reserved. Do not access locations in these regions.
2. Do not use addresses 20000h to 23FFFh because these areas are used for the emulator debugger. Refer to **23. Notes on Emulator Debugger** of Hardware Manual.

Part Number	Internal ROM			Internal RAM		
	Size	Address 0YYYYh	Address ZZZZZh	Size	Address 0XXXXh	Address 0SSSSh
R5F21206JFP, R5F21206KFP	32 Kbytes	08000h	-	2 Kbytes	00BFFh	-
R5F21207JFP, R5F21207KFP	48 Kbytes	04000h	-	2.5 Kbytes	00DFFh	-
R5F21208JFP, R5F21208KFP	64 Kbytes	04000h	13FFFh	3 Kbytes	00FFFh	-
R5F2120AJFP, R5F2120AKFP	96 Kbytes	04000h	1BFFFh	5 Kbytes	00FFFh	037FFh
R5F2120CJFP, R5F2120CKFP	128 Kbytes	04000h	23FFFh	6 Kbytes	00FFFh	03BFFh

Figure 3.1 Memory Map of R8C/20 Group

3.2 R8C/21 Group

Figure 3.2 shows a Memory Map of R8C/21 Group. The R8C/21 Group has 1 Mbyte of address space from address 00000h to FFFFFh.
The internal ROM (program ROM) is allocated lower addresses, beginning with address 0FFFFh. For example, a 48-Kbyte internal ROM is allocated addresses 04000h to 0FFFFh.
The fixed interrupt vector table is allocated addresses 0FFDCh to 0FFFFh. They store the starting address of each interrupt routine.
The internal ROM (data flash) is allocated addresses 02400h to 02BFFh.
The internal RAM is allocated higher addresses, beginning with address 00400h. For example, a 2.5-Kbyte internal RAM is allocated addresses 00400h to 00DFFh. The internal RAM is used not only for storing data but also for calling subroutines and as stacks when interrupt requests are acknowledged.
Special function registers (SFR) are allocated addresses 00000h to 002FFh. The peripheral function control registers are allocated them. All addresses within the SFR, which have nothing allocated are reserved for future use and cannot be accessed by users.



NOTES:
1. Data flash block A (1 Kbyte) and B (1 Kbyte) are shown.
2. The blank regions are reserved. Do not access locations in these regions.
3. Do not use addresses 20000h to 23FFFh because these areas are used for the emulator debugger. Refer to **23. Notes on Emulator Debugger** of Hardware Manual.

Part Number	Internal ROM			Internal RAM		
	Size	Address 0YYYYh	Address ZZZZZh	Size	Address 0XXXXh	Address 0SSSSh
R5F21216JFP, R5F21216KFP	32 Kbytes	08000h	-	2 Kbytes	00BFFh	-
R5F21217JFP, R5F21217KFP	48 Kbytes	04000h	-	2.5 Kbytes	00DFFh	-
R5F21218JFP, R5F21218KFP	64 Kbytes	04000h	13FFFh	3 Kbytes	00FFFh	-
R5F2121AJFP, R5F2121AKFP	96 Kbytes	04000h	1BFFFh	5 Kbytes	00FFFh	037FFh
R5F2121CJFP, R5F2121CKFP	128 Kbytes	04000h	23FFFh	6 Kbytes	00FFFh	03BFFh

Figure 3.2 Memory Map of R8C/21 Group

Table 4.5 SFR Information (5)(1)

Address	Register	Symbol	After reset
0100h	Timer RA Control Register	TRACR	00h
0101h	Timer RA I/O Control Register	TRAIOC	00h
0102h	Timer RA Mode Register	TRAMR	00h
0103h	Timer RA Prescaler Register	TRAPRE	FFh
0104h	Timer RA Register	TRA	FFh
0105h			
0106h	LIN Control Register	LINCR	00h
0107h	LIN Status Register	LINST	00h
0108h	Timer RB Control Register	TRBCR	00h
0109h	Timer RB One-Shot Control Register	TRBOCR	00h
010Ah	Timer RB I/O Control Register	TRBIOC	00h
010Bh	Timer RB Mode Register	TRBMR	00h
010Ch	Timer RB Prescaler Register	TRBPRE	FFh
010Dh	Timer RB Secondary Register	TRBSC	FFh
010Eh	Timer RB Primary	TRBPR	FFh
010Fh			
0110h			
0111h			
0112h			
0113h			
0114h			
0115h			
0116h			
0117h			
0118h	Timer RE Counter Data Register	TRESEC	00h
0119h	Timer RE Compare Data Register	TREMIN	00h
011Ah			
011Bh			
011Ch	Timer RE Control Register 1	TRECR1	00h
011Dh	Timer RE Control Register 2	TRECR2	00h
011Eh	Timer RE Count Source Select Register	TRECSR	00001000b
011Fh			
0120h			
0121h			
0122h			
0123h			
0124h			
0125h			
0126h			
0127h			
0128h			
0129h			
012Ah			
012Bh			
012Ch			
012Dh			
012Eh			
012Fh			
0130h			
0131h			
0132h			
0133h			
0134h			
0135h			
0136h			
0137h	Timer RD Start Register	TRDSTR	11111100b
0138h	Timer RD Mode Register	TRDMR	00001110b
0139h	Timer RD PWM Mode Register	TRDPMR	10001000b
013Ah	Timer RD Function Control Register	TRDFCR	10000000b
013Bh	Timer RD Output Master Enable Register 1	TRDOER1	FFh
013Ch	Timer RD Output Master Enable Register 2	TRDOER2	01111111b
013Dh	Timer RD Output Control Register	TRDOCR	00h
013Eh	Timer RD Digital Filter Function Select Register 0	TRDDF0	00h
013Fh	Timer RD Digital Filter Function Select Register 1	TRDDF1	00h

X: Undefined

NOTE:

1. The blank regions are reserved. Do not access locations in these regions.

5. Electrical Characteristics

Table 5.1 Absolute Maximum Ratings

Symbol	Parameter	Condition	Rated value	Unit
V_{CC}/AV_{CC}	Supply voltage		-0.3 to 6.5	V
V_I	Input voltage		-0.3 to V_{CC}+0.3	V
V_O	Output voltage		-0.3 to V_{CC}+0.3	V
P_d	Power dissipation	-40°C ≤ Topr ≤ 85°C	300	mW
		85°C < Topr ≤ 125°C	125	mW
T_{opr}	Operating ambient temperature		-40 to 85 (J version) / -40 to 125 (K version)	°C
T_{stg}	Storage temperature		-65 to 150	°C

Table 5.2 Recommended Operating Conditions

Symbol	Parameter		Conditions	Standard			Unit
				Min.	Typ.	Max.	
V_{CC}/AV_{CC}	Supply voltage			2.7	–	5.5	V
V_{SS}/AV_{CC}	Supply voltage			–	0	–	V
V_{IH}	Input “H” voltage			0.8V_{CC}	–	V_{CC}	V
V_{IL}	Input “L” voltage			0	–	0.2V_{CC}	V
$I_{OH(sum)}$	Peak sum output “H” current	Sum of all Pins $I_{OH\ (peak)}$		–	–	-60	mA
$I_{OH(peak)}$	Peak output “H” current			–	–	-10	mA
$I_{OH(avg)}$	Average output “H” current			–	–	-5	mA
$I_{OL(sum)}$	Peak sum output “L” currents	Sum of all Pins $I_{OL\ (peak)}$		–	–	60	mA
$I_{OL(peak)}$	Peak output “L” currents			–	–	10	mA
$I_{OL(avg)}$	Average output “L” current			–	–	5	mA
$f_{(XIN)}$	XIN clock input oscillation frequency		3.0 V ≤ V_{CC} ≤ 5.5 V -40°C ≤ Topr ≤ 85°C	0	–	20	MHz
			3.0 V ≤ V_{CC} ≤ 5.5 V -40°C ≤ Topr ≤ 125°C	0	–	16	MHz
			2.7 V ≤ V_{CC} < 3.0 V	0	–	10	MHz
–	System clock	OCD2 = 0 When XIN clock is selected.	3.0 V ≤ V_{CC} ≤ 5.5 V -40°C ≤ Topr ≤ 85°C	0	–	20	MHz
			3.0 V ≤ V_{CC} ≤ 5.5 V -40°C ≤ Topr ≤ 125°C	0	–	16	MHz
			2.7 V ≤ V_{CC} < 3.0 V	0	–	10	MHz
		OCD2 = 1 When on-chip oscillator clock is selected.	FRA01 = 0 When low-speed on-chip oscillator clock is selected.	–	125	–	kHz
			FRA01 = 1 When high-speed on-chip oscillator clock is selected. 3.0 V ≤ V_{CC} ≤ 5.5 V -40°C ≤ Topr ≤ 85°C	–	–	20	MHz
			FRA01 = 1 When high-speed on-chip oscillator clock is selected.	–	–	10	MHz

NOTES:
1. V_{CC} = 2.7 to 5.5 V at Topr = -40 to 85°C (J version) / -40 to 125°C (K version), unless otherwise specified.
2. The average output current indicates the average value of current measured during 100 ms.

Table 5.4 Flash Memory (Program ROM) Electrical Characteristics

Symbol	Parameter	Conditions	Standard			Unit
			Min.	Typ.	Max.	
–	Program/erase endurance(2)	R8C/20 Group	100(3)	–	–	times
		R8C/21 Group	1,000(3)	–	–	times
–	Byte program time		–	50	400	µs
–	Block erase time		–	0.4	9	s
$t_{d(SR-SUS)}$	Time delay from suspend request until erase suspend		–	–	97 + CPU clock × 6 cycle	µs
–	Interval from erase start/restart until following suspend request		650	–	–	µs
–	Interval from program start/restart until following suspend request		0	–	–	ns
–	Time from suspend until program/erase restart		–	–	3 + CPU clock × 4 cycle	µs
–	Program, erase voltage		2.7	–	5.5	V
–	Read voltage		2.7	–	5.5	V
–	Program, erase temperature		0	–	60	°C
–	Data hold time(7)	Ambient temperature = 55°C	20	–	–	year

NOTES:
1. V_{CC} = 2.7 to 5.5 V at Topr = -40 to 85°C (J version) / -40 to 125°C (K version), unless otherwise specified.
2. Definition of programming/erasure endurance
   The programming and erasure endurance is defined on a per-block basis.
   If the programming and erasure endurance is n (n = 100 or 1,000), each block can be erased n times.
   For example, if 1,024 1-byte writes are performed to different addresses in block A, a 1 Kbyte block, and then the block is erased, the programming/erasure endurance still stands at one. However, the same address must not be programmed more than once per erase operation (overwriting prohibited).
3. Endurance to guarantee all electrical characteristics after program and erase (1 to Min. value can be guaranteed).
4. In a system that executes multiple programming operations, the actual erasure endurance can be reduced by writing to sequential addresses in turn so that as much of the block as possible is used up before performing an erase operation. For example, when programming groups of 16 bytes, the effective number of rewrites can be minimized by programming up to 128 groups before erasing them all in one operation. It is also advisable to retain data on the erasure endurance of each block and limit the number of erase operations to a certain number.
5. If error occurs during block erase, attempt to execute the clear status register command, then the block erase command at least three times until the erase error does not occur.
6. Customers desiring program/erase failure rate information should contact their Renesas technical support representative.
7. The data hold time includes time that the power supply is off or the clock is not supplied.

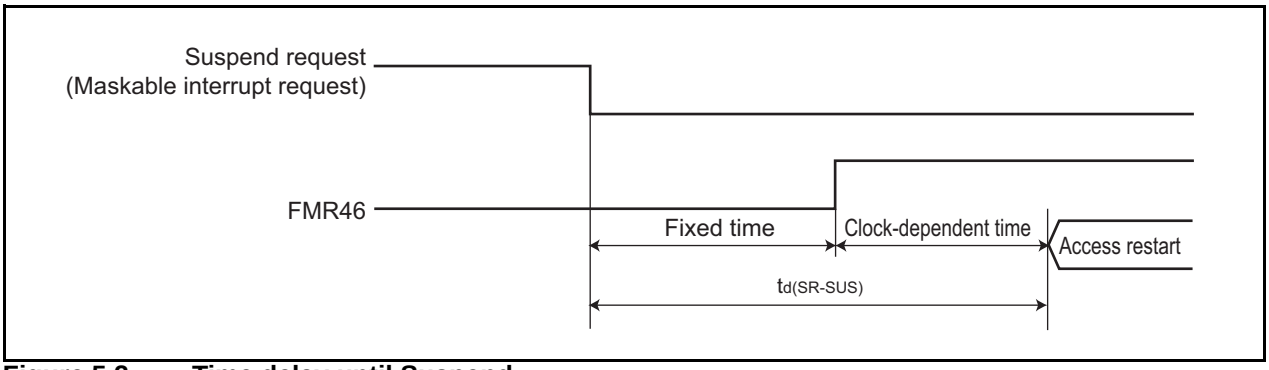


Figure 5.2 Time delay until Suspend

Table 5.6 Voltage Detection 1 Circuit Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
V_{det1}	Voltage detection level(3, 4)		2.70	2.85	3.00	V
$t_{d(Vdet1-A)}$	Voltage monitor 1 reset generation time(5)		–	40	200	µs
–	Voltage detection circuit self power consumption	VCA26 = 1, V_{CC} = 5.0 V	–	0.6	–	µA
$t_{d(E-A)}$	Waiting time until voltage detection circuit operation starts(2)		–	–	100	µs
Vccmin	MCU operating voltage minimum value		2.70	–	–	V

NOTES:
1. The measurement condition is V_{CC} = 2.7 V to 5.5 V and Topr = -40°C to 85°C (J version) / -40°C to 125°C (K version).
2. Necessary time until the voltage detection circuit operates when setting to 1 again after setting the VCA26 bit in the VCA2 register to 0.
3. Hold $V_{det2} > V_{det1}$.
4. This parameter shows the voltage detection level when the power supply drops. The voltage detection level when the power supply rises is higher than the voltage detection level when the power supply drops by approximately 0.1 V.
5. Time until the voltage monitor 1 reset is generated after the voltage passes V_{det1} when V_{CC} falls. When using the digital filter, its sampling time is added to $t_{d(Vdet1-A)}$. When using the voltage monitor 1 reset, maintain this time until V_{CC} = 2.0 V after the voltage passes V_{det1} when the power supply falls.

Table 5.7 Voltage Detection 2 Circuit Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
V_{det2}	Voltage detection level(4)		3.3	3.6	3.9	V
$t_{d(Vdet2-A)}$	Voltage monitor 2 reset/interrupt request generation time(2, 5)		–	40	200	µs
–	Voltage detection circuit self power consumption	VCA27 = 1, V_{CC} = 5.0V	–	0.6	–	µA
$t_{d(E-A)}$	Waiting time until voltage detection circuit operation starts(3)		–	–	100	µs

NOTES:
1. The measurement condition is V_{CC} = 2.7 V to 5.5 V and Topr = -40°C to 85°C (J version) / -40°C to 125°C (K version).
2. Time until the voltage monitor 2 reset/interrupt request is generated since the voltage passes V_{det2}.
3. Necessary time until the voltage detection circuit operates when setting to 1 again after setting the VCA27 bit in the VCA2 register to 0.
4. Hold $V_{det2} > V_{det1}$.
5. When using the digital filter, its sampling time is added to $t_{d(Vdet2-A)}$. When using the voltage monitor 2 reset, maintain this time until V_{CC} = 2.0 V after the voltage passes V_{det2} when the power supply falls.

Table 5.9 High-Speed On-Chip Oscillator Circuit Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
fOCO40M	High-speed on-chip oscillator frequency temperature • supply voltage dependence	V_{CC} = 4.75 V to 5.25 V, 0°C ≤ Topr ≤ 60°C(2)	39.2	40	40.8	MHz
		V_{CC} = 3.0 V to 5.25 V, -20°C ≤ Topr ≤ 85°C(2)	38.8	40	41.2	MHz
		V_{CC} = 3.0 V to 5.5 V, -40°C ≤ Topr ≤ 85°C(2)	38.4	40	41.6	MHz
		V_{CC} = 3.0 V to 5.5 V, -40°C ≤ Topr ≤ 125°C(2)	38.0	40	42.0	MHz
		V_{CC} = 2.7 V to 5.5 V, -40°C ≤ Topr ≤ 125°C(2)	37.6	40	42.4	MHz
–	The value of the FRA1 register when the reset is deasserted		08h	40	F7h	–
–	High-speed on-chip oscillator adjustment range	Adjust the FRA1 register to -1 bit (the value when the reset is deasserted)	–	+ 0.3	–	MHz
–	Oscillation stability time		–	10	100	µs
–	Self power consumption when high-speed on-chip oscillator oscillating	V_{CC} = 5.0 V, Topr = 25°C	–	600	–	µA

NOTES:
1. V_{CC} = 2.7 V to 5.5 V, Topr = -40°C to 85°C (J version) / -40°C to 125°C (K version), unless otherwise specified.
2. The standard value shows when the reset is deasserted for the FRA1 register.

Table 5.10 Low-Speed On-Chip Oscillator Circuit Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
fOCO-S	Low-speed on-chip oscillator frequency		40	125	250	kHz
–	Oscillation stability time		–	10	100	µs
–	Self power consumption when low-speed on-chip oscillator oscillating	V_{CC} = 5.0 V, Topr = 25°C	–	15	–	µA

NOTE:
1. V_{CC} = 2.7 V to 5.5 V, Topr = -40°C to 85°C (J version) / -40°C to 125°C (K version), unless otherwise specified.

Table 5.11 Power Supply Circuit Timing Characteristics

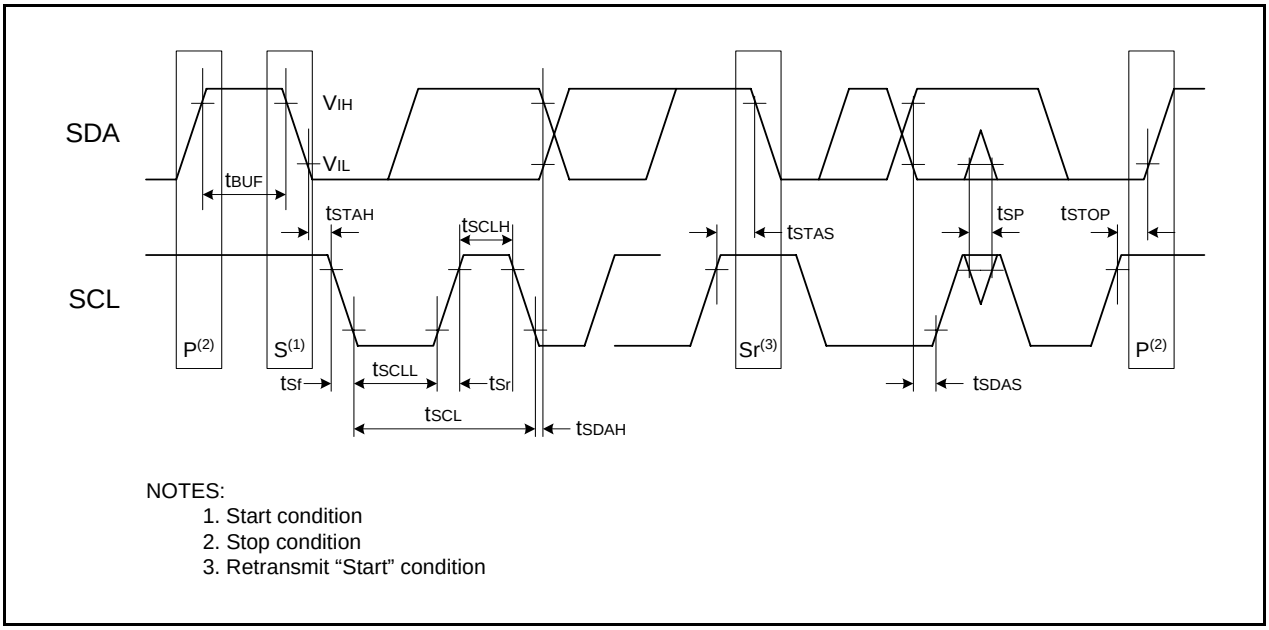
Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
$t_{d(P-R)}$	Time for internal power supply stabilization during power-on(2)		1	–	2000	µs
$t_{d(R-S)}$	STOP exit time(3)		–	–	150	µs

NOTES:
1. The measurement condition is V_{CC} = 2.7 to 5.5 V and Topr = -40°C to 85°C (J version) / -40°C to 125°C (K version), unless otherwise specified.
2. Waiting time until the internal power supply generation circuit stabilizes during power-on.
3. Time until CPU clock supply starts since the interrupt is acknowledged to exit stop mode.

Table 5.13 Timing Requirements of I²C Bus Interface(1)

Symbol	Parameter	Conditions	Standard			Unit
			Min.	Typ.	Max.	
t_{SCL}	SCL input cycle time		$12t_{CYC}$ + 600(2)	–	–	ns
t_{SCLH}	SCL input “H” width		$3t_{CYC}$ + 300(2)	–	–	ns
t_{SCLL}	SCL input “L” width		$5t_{CYC}$ + 300(2)	–	–	ns
t_{sf}	SCL, SDA input falling time		–	–	300	ns
t_{SP}	SCL, SDA input spike pulse rejection time		–	–	$1t_{CYC}$(2)	ns
t_{BUF}	SDA input bus-free time		$5t_{CYC}$(2)	–	–	ns
t_{STAH}	Start condition input hole time		$3t_{CYC}$(2)	–	–	ns
t_{STAS}	Retransmit start condition input setup time		$3t_{CYC}$(2)	–	–	ns
t_{STOP}	Stop condition input setup time		$3t_{CYC}$(2)	–	–	ns
t_{SOAS}	Data input setup time		$1t_{CYC}$ + 20(2)	–	–	ns
t_{SDAH}	Data input hold time		0	–	–	ns

NOTES:
1. V_{CC} = 2.7 to 5.5 V, V_{SS} = 0V at Topr = -40 to 85°C (J version) / -40 to 125°C (K version), unless otherwise specified.
2. $1t_{CYC}$ = 1/f1(s)



NOTES:
1. Start condition
2. Stop condition
3. Retransmit “Start” condition

Figure 5.7 I/O Timing of I²C Bus Interface

Table 5.14 Electrical Characteristics (1) [Vcc = 5 V]

Symbol	Parameter		Condition		Standard			Unit
					Min.	Typ.	Max.	
V_{OH}	Output “H” Voltage	Except XOUT	I_{OH} = -5 mA		Vcc – 2.0	–	Vcc	V
			I_{OH} = -200 µA		Vcc – 0.3	–	Vcc	V
		XOUT	Drive capacity HIGH	I_{OH} = -1 mA	Vcc – 2.0	–	Vcc	V
			Drive capacity LOW	I_{OH} = -500 µA	Vcc – 2.0	–	Vcc	V
V_{OL}	Output “L” Voltage	Except XOUT	I_{OL} = 5 mA		–	–	2.0	V
			I_{OL} = 200 µA		–	–	0.45	V
		XOUT	Drive capacity HIGH	I_{OL} = 1 mA	–	–	2.0	V
			Drive capacity LOW	I_{OL} = 500 µA	–	–	2.0	V
V_{T+}-V_{T-}	Hysteresis	$\overline{INT0}$, $\overline{INT1}$, $\overline{INT2}$, $\overline{INT3}$, $\overline{KI0}$, $\overline{KI1}$, $\overline{KI2}$, $\overline{KI3}$, TRAIO, RXD0, RXD1, CLK0, SSI, SCL, SDA, SSO			0.1	0.5	–	V
		$\overline{RESET}$			0.1	1.0	–	V
I_{IH}	Input “H” current		VI = 5 V, Vcc = 5 V		–	–	5.0	µA
I_{IL}	Input “L” current		VI = 0 V, Vcc = 5 V		–	–	-5.0	µA
R_{PULLUP}	Pull-Up Resistance		VI = 0 V, Vcc = 5 V		30	50	167	kΩ
R_{fXIN}	Feedback Resistance	XIN			–	1.0	–	MΩ
V_{RAM}	RAM Hold Voltage		During stop mode		2.0	–	–	V

NOTE:
1. Vcc = 4.2 to 5.5 V at Topr = -40 to 85°C (J version) / -40 to 125°C (K version), f(XIN) = 20 MHz, unless otherwise specified.

Timing Requirements (Unless Otherwise Specified: Vcc = 5 V, Vss = 0 V at Topr = 25°C) [Vcc = 5 V]

Table 5.16 XIN Input

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(XIN)}$	XIN input cycle time	50	–	ns
$t_{WH(XIN)}$	XIN input “H” width	25	–	ns
$t_{WL(XIN)}$	XIN input “L” width	25	–	ns

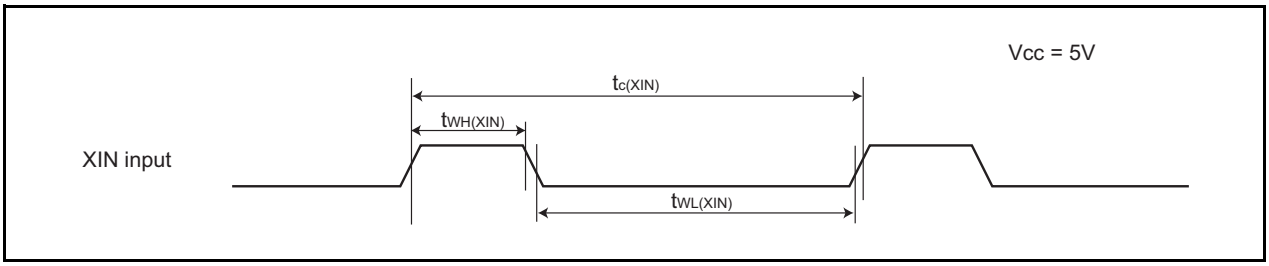


Figure 5.8 XIN Input Timing Diagram when Vcc = 5 V

Table 5.17 TRAIO Input

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(TRAIO)}$	TRAIO input cycle time	100	–	ns
$t_{WH(TRAIO)}$	TRAIO input “H” width	40	–	ns
$t_{WL(TRAIO)}$	TRAIO input “L” width	40	–	ns

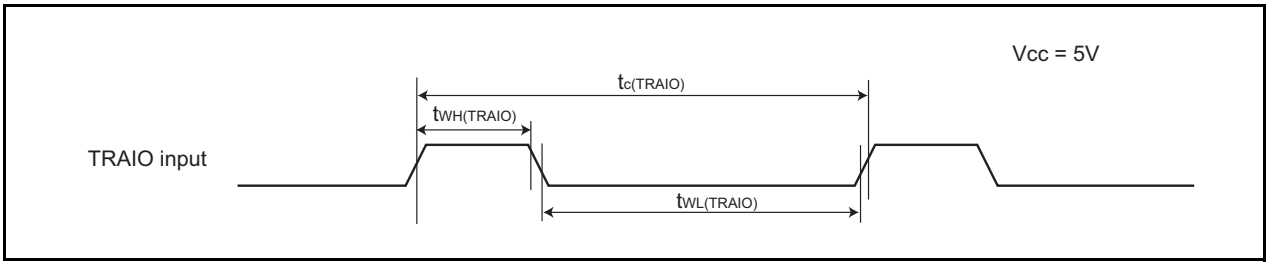


Figure 5.9 TRAIO Input Timing Diagram when Vcc = 5 V

Table 5.20 Electrical Characteristics (3) [Vcc = 3 V]

Symbol	Parameter		Condition		Standard			Unit
					Min.	Typ.	Max.	
V_{OH}	Output “H” voltage	Except XOUT	I_{OH} = -1 mA		Vcc – 0.5	–	Vcc	V
		XOUT	Drive capacity HIGH	I_{OH} = -0.1 mA	Vcc – 0.5	–	Vcc	V
			Drive capacity LOW	I_{OH} = -50 μA	Vcc – 0.5	–	Vcc	V
V_{OL}	Output “L” voltage	Except XOUT	I_{OL} = 1 mA		–	–	0.5	V
		XOUT	Drive capacity HIGH	I_{OL} = 0.1 mA	–	–	0.5	V
			Drive capacity LOW	I_{OL} = 50 μA	–	–	0.5	V
V_{T+}-V_{T-}	Hysteresis	$\overline{INT0}$, $\overline{INT1}$, $\overline{INT2}$, $\overline{INT3}$, $\overline{KI0}$, $\overline{KI1}$, $\overline{KI2}$, $\overline{KI3}$, TRAIO, RXD0, RXD1, CLK0, SSI, SCL, SDA, SSO			0.1	0.3	–	V
		$\overline{RESET}$			0.1	0.4	–	V
I_{IH}	Input “H” current		VI = 3 V, Vcc = 3 V		–	–	4.0	μA
I_{IL}	Input “L” current		VI = 0 V, Vcc = 3 V		–	–	-4.0	μA
R_{PULLUP}	Pull-up resistance		VI = 0 V, Vcc = 3 V		66	160	500	kΩ
R_{fXIN}	Feedback resistance	XIN			–	3.0	–	MΩ
V_{RAM}	RAM hold voltage		During stop mode		2.0	–	–	V

NOTE:
1. Vcc = 2.7 to 3.3 V at Topr = -40 to 85°C (J version) / -40 to 125°C (K version), f(XIN) = 10 MHz, unless otherwise specified.

Table 5.24 Serial Interface

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(CK)}$	CLK0 input cycle time	300	–	ns
$t_{W(CKH)}$	CLK0 input “H” width	150	–	ns
$t_{W(CKL)}$	CLK0 input “L” width	150	–	ns
$t_{d(C-Q)}$	TXDi output delay time	–	80	ns
$t_{h(C-Q)}$	TXDi hold time	0	–	ns
$t_{su(D-C)}$	RXDi input setup time	70	–	ns
$t_{h(C-D)}$	RXDi input hold time	90	–	ns

i = 0 or 1

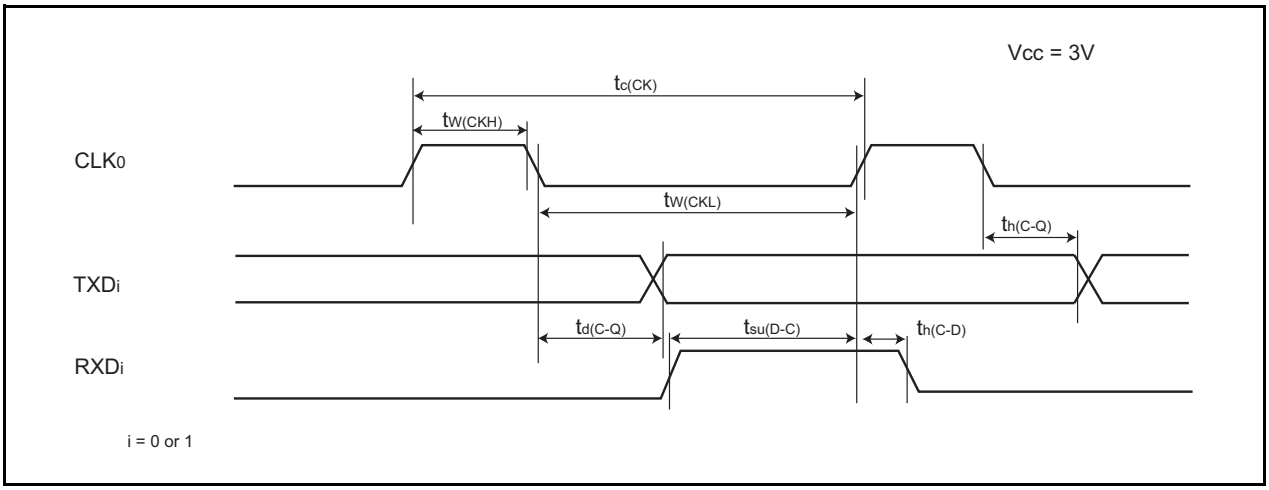


Figure 5.14 Serial Interface Timing Diagram when Vcc = 3 V

Table 5.25 External Interrupt $\overline{INTi}$ (i = 0 to 3) Input

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{W(INH)}$	$\overline{INTi}$ input “H” width	380(1)	–	ns
$t_{W(INL)}$	$\overline{INTi}$ input “L” width	380(2)	–	ns

NOTES:
1. When selecting the digital filter by the $\overline{INTi}$ input filter select bit, use the $\overline{INTi}$ input HIGH width to the greater value, either (1/digital filter clock frequency x 3) or the minimum value of standard.
2. When selecting the digital filter by the $\overline{INTi}$ input filter select bit, use the $\overline{INTi}$ input LOW width to the greater value, either (1/digital filter clock frequency x 3) or the minimum value of standard.

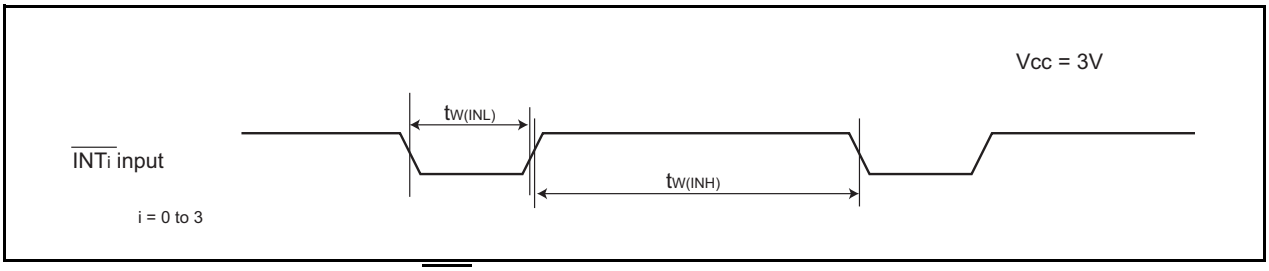
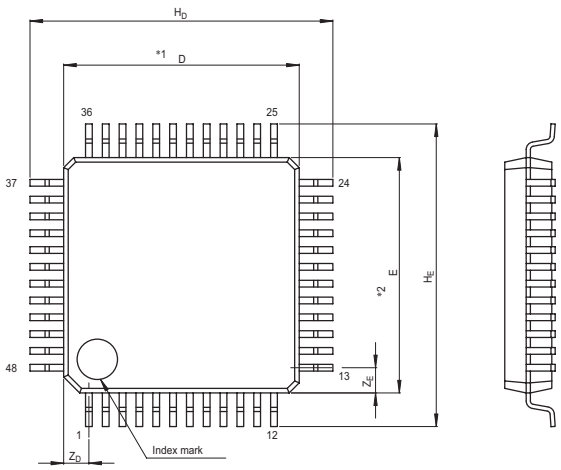


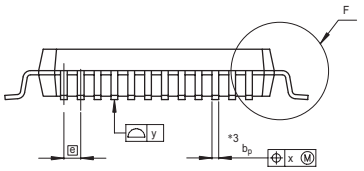
Figure 5.15 External Interrupt $\overline{INTi}$ Input Timing Diagram when Vcc = 3 V (i = 0 to 3)

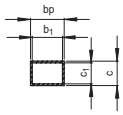
Package Dimensions

Diagrams showing the latest package dimensions and mounting information are available in the “Packages” section of the Renesas Technology website.

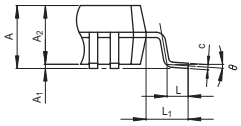
JEITA Package Code	RENESAS Code	Previous Code	MASS[Typ.]
P-LQFP48-7x7-0.50	PLQP0048KB-A	48P6Q-A	0.2g







Terminal cross section



Detail F

NOTE)
1. DIMENSIONS "*1" AND "*2" DO NOT INCLUDE MOLD FLASH.
2. DIMENSION "*3" DOES NOT INCLUDE TRIM OFFSET.

Reference Symbol	Dimension in Millimeters		
	Min	Nom	Max
D	6.9	7.0	7.1
E	6.9	7.0	7.1
A_2	—	1.4	—
H_D	8.8	9.0	9.2
H_E	8.8	9.0	9.2
A	—	—	1.7
A_1	0	0.1	0.2
b_p	0.17	0.22	0.27
b_1	—	0.20	—
c	0.09	0.145	0.20
c_1	—	0.125	—
θ	0°	—	8°
e	—	0.5	—
x	—	—	0.08
y	—	—	0.10
Z_D	—	0.75	—
Z_E	—	0.75	—
L	0.35	0.5	0.65
L_1	—	1.0	—

REVISION HISTORY	R8C/20 Group, R8C/21 Group Datasheet

Rev.	Date	Description	
		Page	Summary
0.20	Sep 29, 2005	20	Table 4.6 SFR Information (6) revised - 0145h: POCR0 → TRDPOCR0 - 0146h, 0147h: TRDCNT0 → TRD0 - 0148h, 0149h: GRA0 → TRDGRA0 - 014Ah, 014Bh: GRB0 → TRDGRB0 - 014Ch, 014Dh: GRC0 → TRDGRC0 - 014Eh, 014Fh: GRD0 → TRDGRD0 - 0155h: POCR1 -> TRDPOCR1 - 0156h, 0157h: TRDCNT1 → TRD1 - 0158h, 0159h: GRA1 → TRDGRA1 - 015Ah, 015Bh: GRB1 → TRDGRB1 - 015Ch, 015Dh: GRC1 → TRDGRC1 - 015Eh, 015Fh: GRD1 → TRDGRD1
		22	5. Electrical Characteristics added
1.00	Nov 15, 2006	All pages	"Preliminary" and "Under development" deleted
		2	Table 1.1 Functions and Specifications for R8C/20 Group revised. NOTE1 deleted.
		3	Table 1.2 Functions and Specifications for R8C/21 Group revised. NOTE1 deleted.
		5	Table 1.3 Product Information for R8C/20 Group; "R5F2120AJFP (D)", "R5F2120CJFP (D)", "R5F2120AKFP (D)", "R5F2120CKFP (D)", and NOTE added. Figure 1.2 Type Number, Memory Size, and Package of R8C/20 Group; "A: 96 KB" and "C: 128 KB" added.
		6	Table 1.4 Product Information for R8C/21 Group; "R5F2121AJFP (D)", "R5F2121CJFP (D)", "R5F2121AKFP (D)", "R5F2121CKFP (D)", and NOTE added. Figure 1.3 Type Number, Memory Size, and Package of R8C/21 Group; "A: 96 KB" and "C: 128 KB" added.
		13	Figure 3.1 Memory Map of R8C/20 Group revised.
		14	Figure 3.2 Memory Map of R8C/21 Group revised.
		15	Table 4.1 SFR Information (1)(1); NOTE8; "The CSPROINI bit in the OFS register is set to 0." → "The CSPROINI bit in the OFS register is 0." revised.
		21	Table 5.1 Absolute Maximum Ratings; Power dissipation revised. Table 5.2 Recommended Operating Conditions; System clock revised.
		26	Table 5.8 Voltage Monitor 1 Reset Circuit Electrical Characteristics → Table 5.8 Power-on Reset Circuit, Voltage Monitor 1 Reset Circuit Electrical Characteristics(1) replaced. Table 5.8 revised. NOTE3 added. Table 5.9 Power-on Reset Circuit Electrical Characteristics deleted. Figure 5.3 Power-on Reset Circuit Electrical Characteristics revised.
		27	Table 5.10 High-Speed On-Chip Oscillator Circuit Electrical Characteristics → Table 5.9 High-Speed On-Chip Oscillator Circuit Electrical Characteristics revised.

REVISION HISTORY	R8C/20 Group, R8C/21 Group Datasheet

Rev.	Date	Description	
		Page	Summary
1.00	Nov 15, 2006	33	Table 5.15 Electrical Characteristics (1) [VCC = 5 V] → Table 5.14 Electrical Characteristics (1) [VCC = 5 V] revised. RAM Hold Voltage, Min.; “1.8” → “2.0” corrected.
		34	Table 5.16 Electrical Characteristics (2) [Vcc = 5 V] → Table 5.15 Electrical Characteristics (2) [Vcc = 5 V] revised. Wait mode revised.
		37	Table 5.21 Electrical Characteristics (3) [VCC = 3 V → Table 5.20 Electrical Characteristics (3) [VCC = 3 V] revised. RAM hold voltage, Min.;“1.8” → “2.0” corrected.
		38	Table 5.22 Electrical Characteristics (4) [Vcc = 3 V] → Table 5.21 Electrical Characteristics (4) [Vcc = 3 V] revised. Wait mode revised.
2.00	Aug 27, 2008	–	“RENESAS TECHNICAL UPDATE” reflected: TN-16C-A172A/E
		5, 6	Table 1.3, Table 1.4 revised Figure 1.2, Figure 1.3; ROM number “XXX” added
		13, 14	Figure 3.1, Figure 3.2; “Expanding area” deleted
		21	Table 5.2; NOTE2 revised
		23	Table 5.4; NOTE2 and NOTE4 revised
		24	Table 5.5; NOTE2 and NOTE5 revised
		25	Table 5.6; “td(Vdet1-A)” added, NOTE5 added Table 5.7; “td(Vdet2-A)” and NOTE2 revised, NOTE5 added
		26	Table 5.8; “trth” and NOTE2 revised Figure 5.3 revised

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